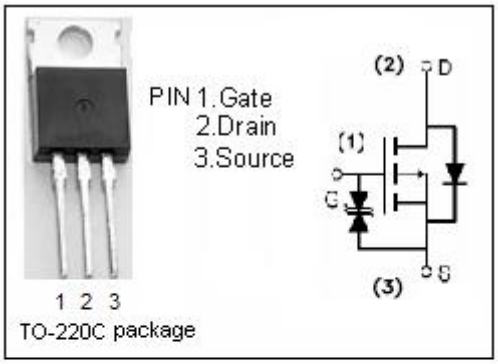
isc P-Channel MOSFET Transistor 2SJ126



DESCRIPTION

- Low Drain-Source ON Resistance
- High Forward Transfer Admittance
- Low Leakage Current
- Enhancement-Mode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

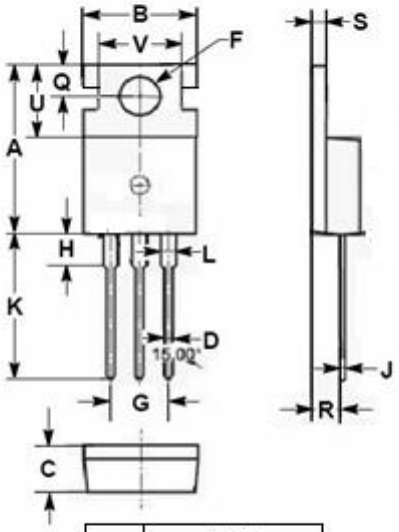
- High speed switching application
- Switching regulator ,DC-DC converter and Motor drive application

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=37℃	-10	A
P_{tot}	Total Dissipation@TC=25℃	40	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.1	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	75	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= -10mA	-60		V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= -1mA	-1.5	-3.5	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= -10V; I_D= -5A		0.4	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= -20V;V_{DS}= 0		-100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -60V,V_{GS}= 0		-1	mA
V_{SD}	Diode Forward Voltage	I_F=-10 A;V_{GS}= 0		-4.5	V